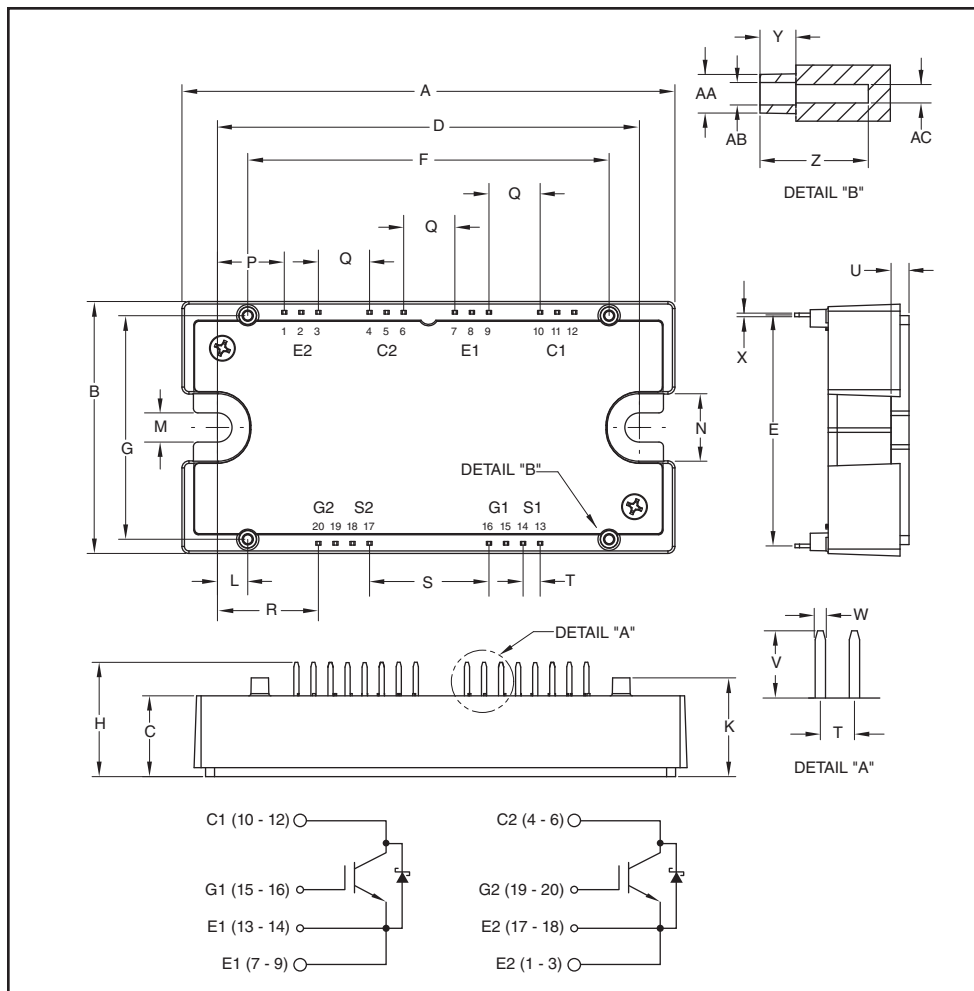


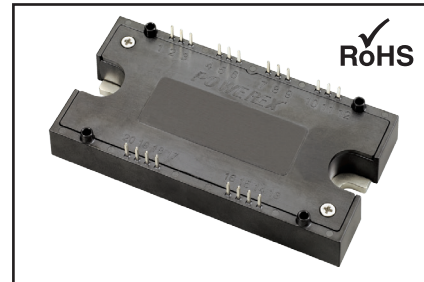
Split Dual Si/SiC Hybrid IGBT Module 100 Amperes/1200 Volts



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.32	109.8
B	2.21	56.1
C	0.71	18.0
D	3.70±0.02	94.0±0.5
E	2.026	51.46
F	3.17	80.5
G	1.96	49.8
H	1.00	25.5
K	0.87	22.0
L	0.266	6.75
M	0.26	6.5
N	0.59	15.0
P	0.586	14.89

Dimensions	Inches	Millimeters
Q	0.449	11.40
R	0.885	22.49
S	1.047	26.6
T	0.15	3.80
U	0.16	4.0
V	0.30	7.5
W	0.045	1.15
X	0.03	0.8
Y	0.16	4.0
Z	0.47	12.1
AA	0.17 Dia.	4.3 Dia.
AB	0.10 Dia.	2.5 Dia.
AC	0.08 Dia.	2.1 Dia.



Description:

Powerex IGBT Modules are designed for use in high frequency applications; upwards of 30 kHz for hard switching applications and 80 kHz for soft switching applications. Each module consists of two IGBT Transistors with each transistor having a reverse-connected super-fast recovery free-wheel silicon carbide Schottky diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low ESW(off)
- ☐ Aluminum Nitride Isolation
- ☐ **Discrete Super-Fast Recovery Free-Wheel Silicon Carbide Schottky Diode**
- ☐ Low Internal Inductance
- ☐ 2 Individual Switches per Module
- ☐ Isolated Baseplate for Easy Heat Sinking
- ☐ AlSiC Baseplate
- ☐ RoHS Compliant

Applications:

- ☐ Energy Saving Power Systems such as:
Fans; Pumps; Consumer Appliances
- ☐ High Frequency Type Power Systems such as:
UPS; High Speed Motor Drives; Induction Heating; Welder; Robotics
- ☐ High Temperature Power Systems such as:
Power Electronics in Electric Vehicle and Aviation Systems

QID1210006
Split Dual Si/SiC Hybrid IGBT Module

100 Amperes/1200 Volts

Absolute Maximum Ratings, $T_j = 25^\circ\text{C}$ unless otherwise specified

Ratings	Symbol	QID1210006	Units
Junction Temperature	T_j	-40 to 150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-40 to 150	$^\circ\text{C}$
Collector-Emitter Voltage (G-E Short)	V_{CES}	1200	Volts
Gate-Emitter Voltage (C-E Short)	V_{GES}	± 20	Volts
Collector Current ($T_C = 25^\circ\text{C}$)	I_C	100*	Amperes
Peak Collector Current	I_{CM}	200*	Amperes
Emitter Current** ($T_C = 25^\circ\text{C}$)	I_E	80*	Amperes
Repetitive Peak Emitter Current ($T_C = 25^\circ\text{C}$, $t_p = 10\text{ms}$, Half Sine Pulse)**	I_{EM}	455*	Amperes
Maximum Collector Dissipation ($T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$)	P_C	570	Watts
Mounting Torque, M6 Mounting	—	40	in-lb
Weight	—	130	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{ISO}	2500	Volts

IGBT Electrical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics		Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current		I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$	—	—	1.0	mA
Gate Leakage Current		I_{GES}	$V_{GE} = V_{GES}$, $V_{CE} = 0V$	—	—	0.5	μA
Gate-Emitter Threshold Voltage		$V_{GE(th)}$	$I_C = 10mA$, $V_{CE} = 10V$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 100A$, $V_{GE} = 15V$, $T_j = 25^{\circ}C$	—	5.0	6.5	Volts
			$I_C = 100A$, $V_{GE} = 15V$, $T_j = 125^{\circ}C$	—	5.0	—	Volts
Total Gate Charge		Q_G	$V_{CC} = 600V$, $I_C = 100A$, $V_{GE} = 15V$	—	450	—	nC
Input Capacitance		C_{ies}	$V_{CE} = 10V$, $V_{GE} = 0V$	—	—	16	nf
Output Capacitance		C_{oes}		—	—	1.3	nf
Reverse Transfer Capacitance		C_{res}		—	—	0.3	nf
Inductive	Turn-on Delay Time	$t_{d(on)}$	$V_{CC} = 600V$, $I_C = 100A$,	—	—	TBD	ns
Load	Rise Time	t_r	$V_{GE1} = V_{GE2} = 15V$,	—	—	TBD	ns
Switch	Turn-off Delay Time	$t_{d(off)}$	$R_G = 3.1\Omega$,	—	—	TBD	ns
	TimeFall Time	t_f	Inductive Load Switching Operation	—	—	TBD	ns

* Pulse width and repetition rate should be such that device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

**Represents characteristics of the anti-parallel, emitter-to-collector silicon carbide Schottky diode (FWDI).

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Split Dual Si/SiC Hybrid IGBT Module

100 Amperes/1200 Volts

Reverse Schottky Diode Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Diode Forward Voltage	V_{FM}	$I_F = 80\text{A}$, $V_{GS} = -5\text{V}$	—	1.6	2.0	Volts
		$I_F = 80\text{A}$, $V_{GS} = -5\text{V}$, $T_j = 175^\circ\text{C}$	—	2.5	3.2	Volts
Diode Reverse Current	I_R	$V_R = 1200\text{V}$	—	140	800	μA
		$V_R = 1200$, $T_j = 150^\circ\text{C}$	—	260	1600	μA
Diode Capacitive Charge	Q_C	$V_R = 1200\text{V}$, $I_F = 80\text{A}$, $di/dt = 800\text{A}/\mu\text{s}$	—	520	—	nC

Thermal and Mechanical Characteristics, $T_j = 25^\circ\text{C}$ unless otherwise specified

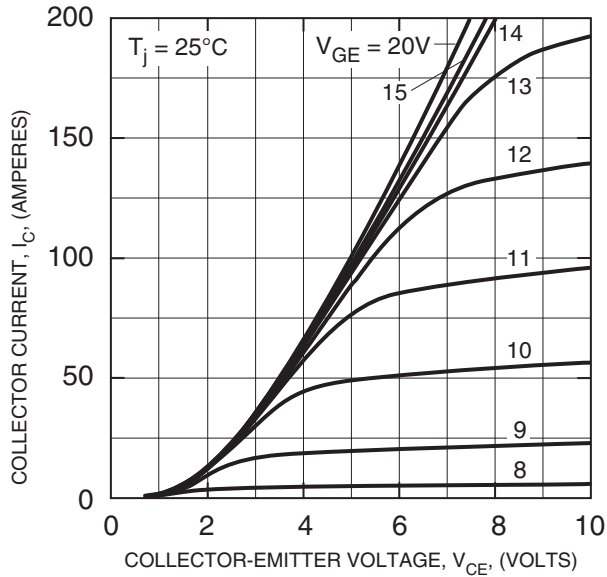
Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)Q}$	Per IGBT 1/2 Module, T_C Reference Point Under Chips	—	—	0.217	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)D}$	Per FWDi 1/2 Module, T_C Reference T_C Reference Point Under Chips	—	—	0.368	$^\circ\text{C}/\text{W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per 1/2 Module, Thermal Grease Applied	—	0.04	—	$^\circ\text{C}/\text{W}$
External Gate Resistance	R_G		3.1	—	31	Ω
Internal Inductance	L_{int}	IGBT Part	—	10	—	nH

QID1210006

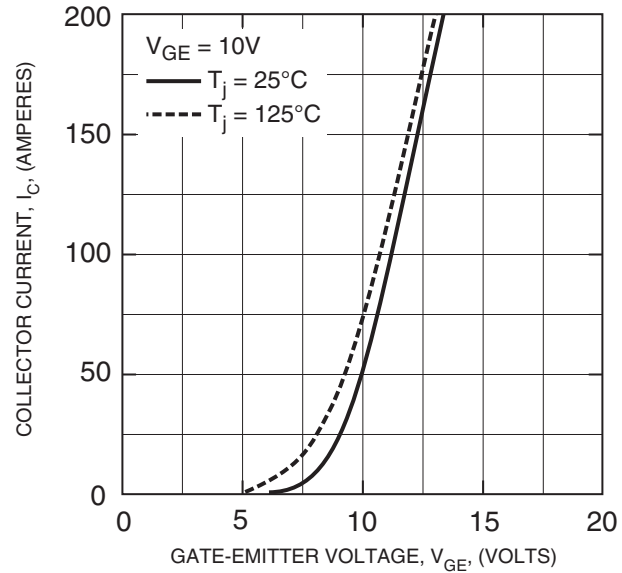
Split Dual Si/SiC Hybrid IGBT Module

100 Amperes/1200 Volts

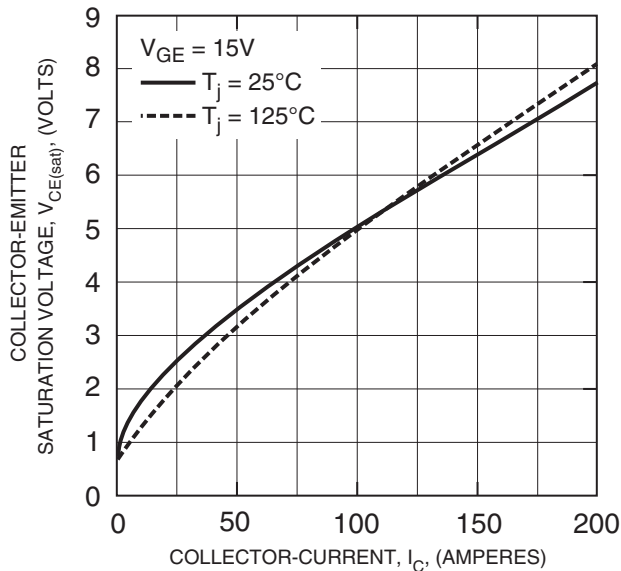
OUTPUT CHARACTERISTICS
(TYPICAL)



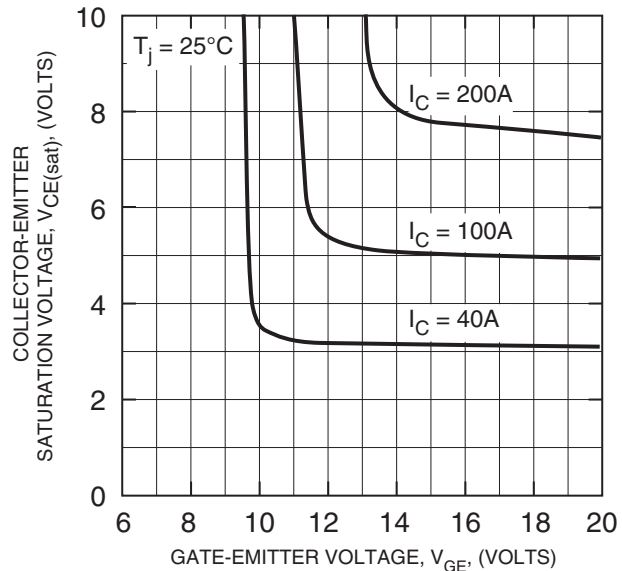
TRANSFER CHARACTERISTICS
(TYPICAL)



COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)

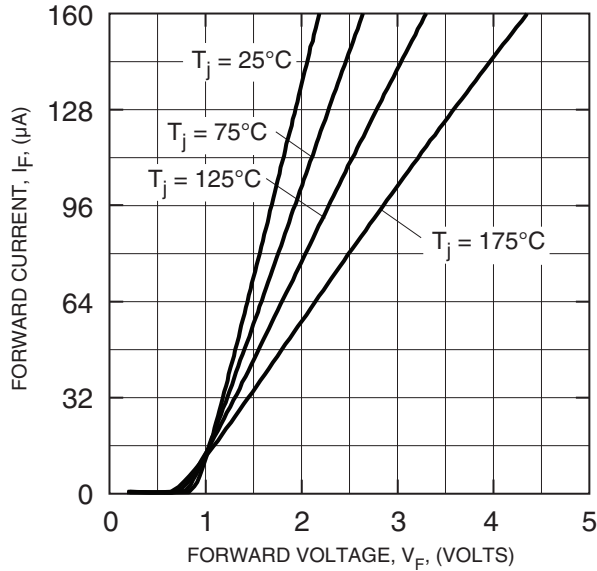


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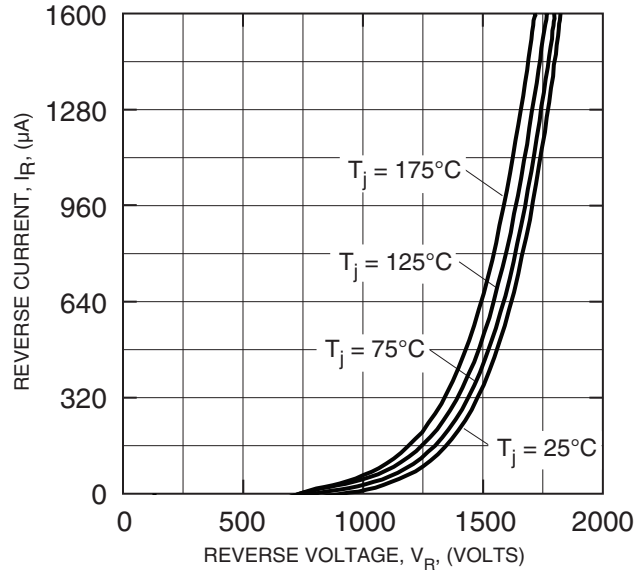
Split Dual Si/SiC Hybrid IGBT Module

100 Amperes/1200 Volts

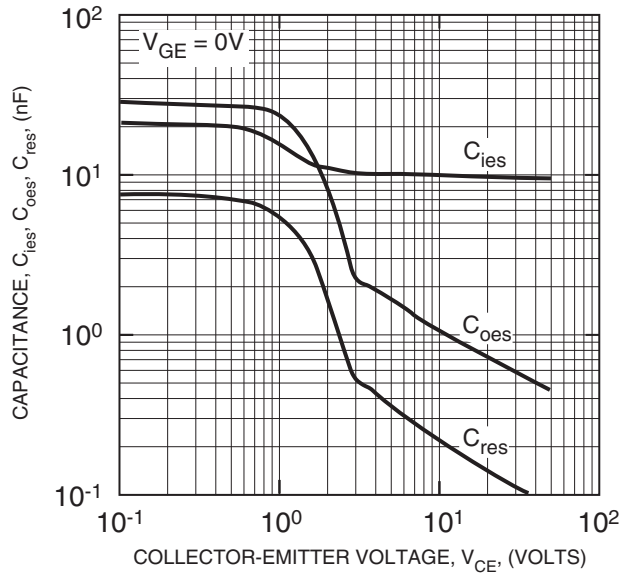
**FREE-WHEEL SCHOTTKY DIODE
FORWARD CHARACTERISTICS
(TYPICAL)**



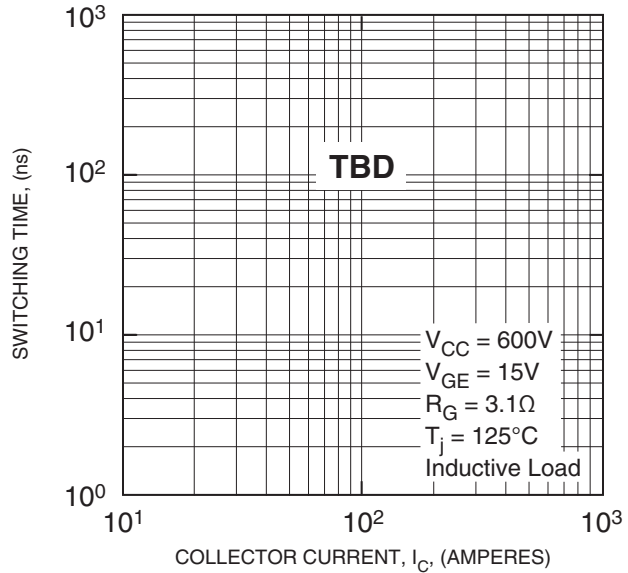
**FREE-WHEEL SCHOTTKY DIODE
REVERSE CHARACTERISTICS
(TYPICAL)**



**CAPACITANCE VS. V_{CE}
(TYPICAL)**



**HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)**

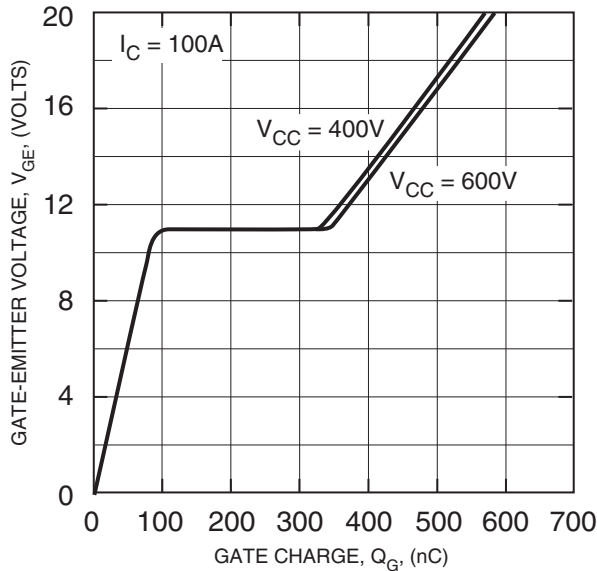


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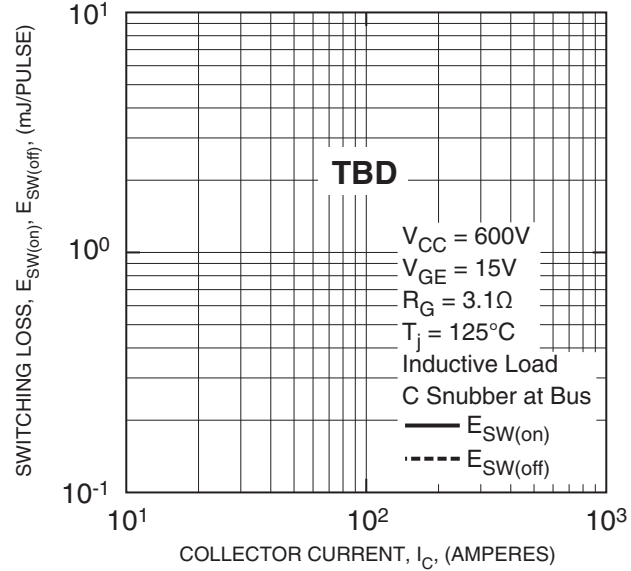
Split Dual Si/SiC Hybrid IGBT Module

100 Amperes/1200 Volts

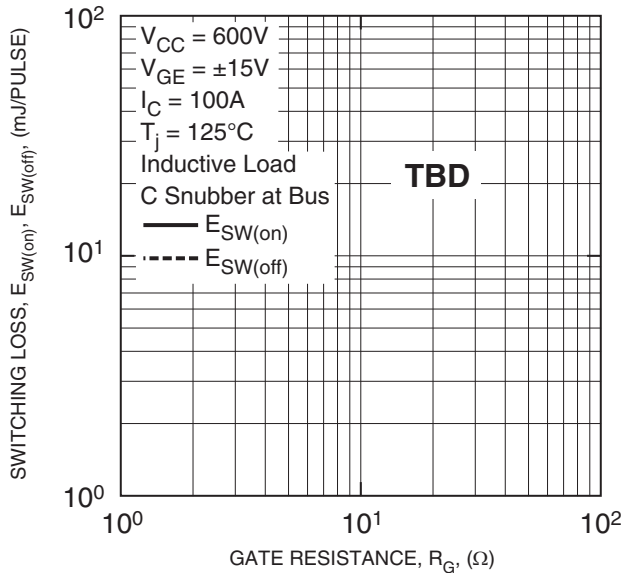
GATE CHARGE VS. V_{GE}



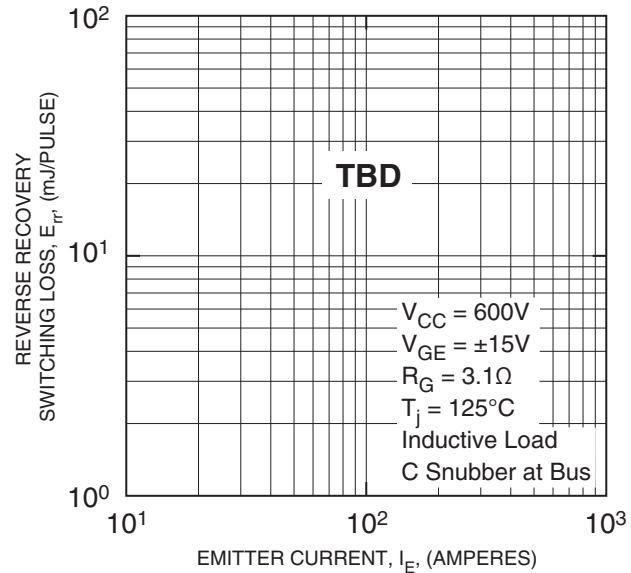
SWITCHING LOSS VS. COLLECTOR CURRENT (TYPICAL)



SWITCHING LOSS VS. GATE RESISTANCE (TYPICAL)



REVERSE RECOVERY SWITCHING LOSS VS. EMITTER CURRENT (TYPICAL)

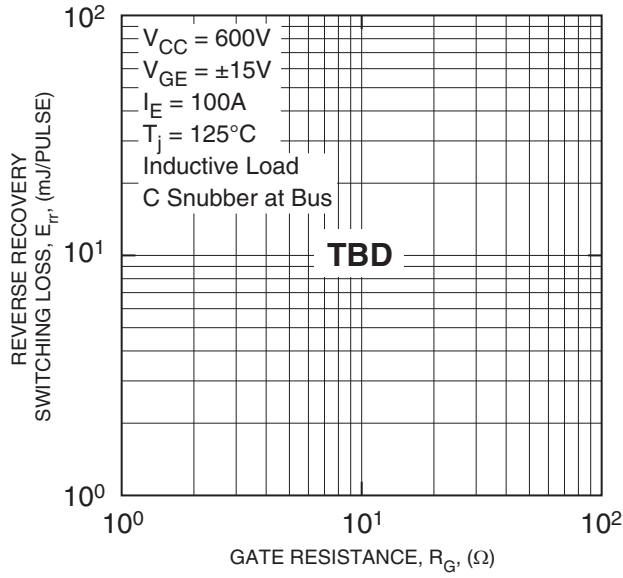


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Split Dual Si/SiC Hybrid IGBT Module

100 Amperes/1200 Volts

REVERSE RECOVERY SWITCHING LOSS VS.
GATE RESISTANCE
(TYPICAL)



TRANSIENT THERMAL
IMPEDANCE CHARACTERISTICS
(IGBT & FWDi)

